Title: METHOD AND APPARATUS FOR IMPROVED COATING OF A SEMICONDUCTOR WAFER

IN THE CLAIMS

Please amend the claims as follows:

- 1-16. (Cancelled)
- 17. (Currently Amended) A method of depositing a material at least-partially along a diameter of a surface having an edge, a center, and an opposite edge, wherein said method comprises: rotating said surface:

providing a nozzle;

positioning said nozzle generally over said edge, wherein said step of positioning said nozzle generally over said edge further comprises:

positioning said nozzle over a first point along a circumference of said surface, and

defining said first point to be independent of a rotation of said surface;

moving said nozzle in no more than one direction along said diameter;

spraying said material from said nozzle while moving said nozzle in a single direction from the first point to a second point of said circumference; and

stopping motion of said nozzle after said nozzle passes over said center, wherein said step of stopping motion of said nozzle further comprises stopping motion of said nozzle when said nozzle is over said opposite edge, and wherein said step of stopping motion of said nozzle when said nozzle is over said opposite edge further comprises:

stopping motion of said nozzle and stopping spraying over a the second point along said circumference, and defining said diameter with said first point, said center, and said second point.

Page 5 Dkt: 303.936US5

- 31. (New) The method of claim 17, wherein rotating said surface includes rotating between 500 and 1500 rpm.
- 32. (New) The method of claim 31, wherein rotating said surface includes rotating in a 50% humidity atmosphere.
- 33. (New) The method of claim 32, wherein rotating said surface includes rotating at 72 degrees F.
- 34. (New) The method of claim 17, wherein spraying said material from said nozzle includes spraying an already rotating wafer.
- 35. (New) The method of claim 17, wherein spraying said material from said nozzle includes dispensing a solution in a fine mist.
- 36. (New) The method of claim 17, wherein spraying said material from said nozzle includes dispensing in a dispersed and divergent pattern.
- 37. (New) The method of claim 17, wherein spraying said material from said nozzle includes spraying an organic solvent.
- 38. (New) The method of claim 17, wherein spraying said material from said nozzle includes spraying a polymer dielectric.
- 39. (New) A method of depositing a wafer-coating, liquid material along a diameter of a wafer surface having a circumferential edge and a center, comprising:

rotating the wafer surface;

providing a nozzle;

positioning the nozzle generally over the edge;

Serial Number: 10/656,745

Filing Date: September 5, 2003
Title: METHOD AND APPARATUS FOR IMPROVED COATING OF A SEMICONDUCTOR WAFER

beginning spraying the wafer-coating material from the nozzle at a first point on a diameter of the wafer:

while spraying, moving the nozzle in a single direction from the first point to a second point on the diameter, over the center point and to the edge of the wafer surface; stopping spraying at the second point.

- 40. (New) The method of claim 39, wherein rotating the wafer surface includes rotating between 500 and 1500 rpm in a 50% humidity atmosphere at 72 degrees F.
- 41. (New) The method of claim 40, wherein spraying the wafer-coating material from the nozzle includes spraying a polymer dielectric.